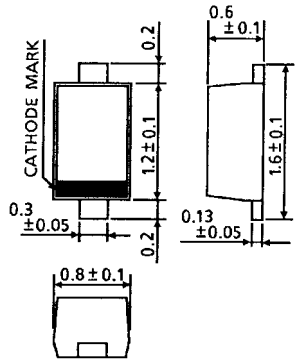
TOSHIBA Diode Silicon Epitaxial Planar Type

1SV329

VCO for UHF Band Radio

Unit: mm

- High capacitance ratio: $C_{1\ V}/C_{4\ V}$ = 2.8 (typ.)
- Low series resistance: r_s = 0.55 Ω (typ.)
- Useful for small size tuner.



ESC

JEDEC	—
JEITA	—
TOSHIBA	1-1G1A

Weight: 0.0014 g (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Reverse voltage	V_R	10	V
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	−55~125	°C

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse voltage	V_R	I_R = 1 μA	10	—	—	V
Reverse current	I_R	V_R = 10 V	—	—	3	nA
Capacitance	$C_{1\ V}$	V_R = 1 V, f = 1 MHz	5.7	—	6.7	pF
Capacitance	$C_{4\ V}$	V_R = 4 V, f = 1 MHz	1.85	—	2.45	pF
Capacitance ratio	$C_{1\ V}/C_{4\ V}$	—	2.7	2.8	—	—
Series resistance	r_s	V_R = 1 V, f = 470 MHz	—	0.55	0.7	Ω

Note: Signal level when capacitance is measured: Vsig = 100 mVrms

Marking